

MiniSKiiP® 2

Twin 6-pack

SKiiP 24ACC12T4V1

Features*

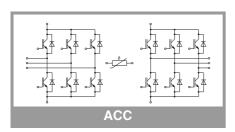
- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

Typical Applications

• 4Q inverters

Remarks

- Max. case temperature limited to T_C=125°C
- Product reliability results valid for T_j≤150°C (recommended T_{j,op}=-40...+150°C)
- Terminal distances sufficient for basic insulation in 3-phase 480VAC TN systems
- DC-link voltage V_{DC}≤800V
- Temperature sensor: no basic insulation to main circuit, signal processing with reference to –DC potential
- Please refer to MiniSKiiP "Technical Explanations" and "Mounting Instructions" for further information
- Inverter IGBT=T1-T12
- Inverse Diode=D1-D12



Absolute	Maximum Rating	s		
Symbol	Conditions		Values	Unit
IGBT 1 - (
V _{CES}				٧
Ic	λ _{paste} =0.8 W/(mK)	T _s = 25 °C		Α
	T _i = 175 °C	T _s = 70 °C		Α
I _C	λ_{paste} =2.5 W/(mK)			Α
	The sie 2.0 Th (Thirt)	T _s = 70 °C		Α
I _{Cnom}		3		Α
I _{CRM}				Α
V _{GES}				V
- GLS				<u> </u>
t _{psc}	$V_{GE} \leq V$		n.c.	μs
	V _{CES} ≤ V			
Tj				°C
IGBT 7 -	12			
V_{CES}	$T_j = 25 ^{\circ}C$		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	38	Α
	T _j = 175 °C	T _s = 70 °C	31	Α
I _C	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	42	Α
	T _j = 175 °C	T _s = 70 °C	35	Α
I _{Cnom}			25	Α
I _{CRM}			75	Α
V _{GES}			-20 20	V
	V _{CC} = 800 V			
t _{psc}	$V_{GE} \le 15 \text{ V}$	T _j = 150 °C	10	μs
т	V _{CES} ≤ 1200 V		-40 175	°C
T _j			-40 175	
Diode 1 -	b	1		
V _{RRM}		T 05.00		V
I _F	λ_{paste} =0.8 W/(mK)	T _s = 25 °C		A
		T _s = 70 °C		A
lF	λ_{paste} =2.5 W/(mK)	T _s = 25 °C		A
		T _s = 70 °C		A
I _{FRM}				A
I _{FSM}	, ,			Α
Tj			175	°C
Diode 7 -				
V_{RRM}	T _j = 25 °C		1200	V
l _F	$\lambda_{paste} = 0.8 \text{ W/(mK)}$	T _s = 25 °C	31	Α
	T _j = 175 °C	T _s = 70 °C	25	Α
l _F	$\lambda_{paste}=2.5 \text{ W/(mK)}$	T _s = 25 °C	34	Α
	T _j = 175 °C	T _s = 70 °C	27	Α
I _{FRM}			50	Α
I _{FSM}	10 ms, sin 180°, T _j	= 150 °C	100	Α
Tj			-40 175	°C
Module				
I _{t(RMS)}	20 A per spring		40	Α
T _{stg}	module without TIN	Л	-40 125	°C
			2500	V



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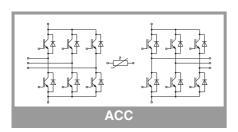
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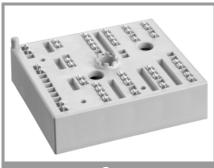
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Characte	eristics					
Symbol	Conditions		min.	typ.	max.	Unit
IGBT 1 - 6	6		•			
V _{CE(sat)}						V
						V
V _{CE0}						V
* CEU	chiplevel					V
r _{CE}						mΩ
						mΩ
$V_{GE(th)}$,					V
I _{CES}					0.3	mA
						mA
C _{ies}						nF
C _{oes}						nF
C_{res}						nF
Q_G						nC
R _{Gint}				0		Ω
t _{d(on)}	_					ns
t _r						ns
E _{on}						mJ
t _{d(off)}	_					ns
t _f	_					ns
E _{off}	$V_{GE} = +15/-15 \text{ V}$					mJ
$R_{th(j-s)}$	per IGBT, λ _{paste} =0.	8 W/(mK)				K/W
R _{th(j-s)}	per IGBT, λ _{paste} =2.	5 W/(mK)				K/W
IGBT 7 - 1	12					
V _{CE(sat)}	$I_{\rm C} = 25 {\rm A}$	T _j = 25 °C		1.85	2.10	V
	V _{GE} = 15 V chiplevel	T _i = 150 °C		2.25	2.45	V
V _{CE0}		T _i = 25 °C		0.80	0.90	V
OLO	chiplevel	T _i = 150 °C		0.70	0.80	V
r _{CE}	V _{GE} = 15 V	T _i = 25 °C		42	48	mΩ
	chiplevel	T _i = 150 °C		62	66	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE} V$, $I_C = 1 \text{ mA}$		5.3	5.8	6.3	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C			1	mA
	V _{CE} = 1200 V			-		mA
C _{ies}	V 05 V	f = 1 MHz		1.45		nF
C _{oes}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		0.12		nF
C_{res}		f = 1 MHz		0.05		nF
Q_{G}	V _{GE} = - 8 V+ 15 V			142		nC
R _{Gint}	T _j = 25 °C			0		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		39		ns
t _r	$I_C = 25 \text{ A}$ $R_{G \text{ on}} = 27 \Omega$	T _j = 150 °C		32		ns
Eon	$R_{G \text{ off}} = 27 \Omega$	T _j = 150 °C		3.2		mJ
t _{d(off)}	$di/dt_{on} = 780 \text{ A/µs}$	T _j = 150 °C		333		ns
t _f	di/dt _{off} = 360 A/μs dv/dt = 3400 V/μs	T _j = 150 °C		91		ns
E _{off}	$V_{GE} = +15/-15 \text{ V}$ $L_s = 21 \text{ nH}$	T _j = 150 °C		3		mJ
R _{th(j-s)}	per IGBT, λ _{paste} =0.	8 W/(mK)		1.13		K/W
R _{th(j-s)}	per IGBT, λ _{paste} =2.			0.94		K/W



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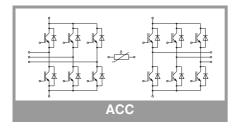
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- Inverse Diode=D1-D12

Characte	ristics					
Symbol	Conditions		min.	typ.	max.	Unit
Diode 1 -	6					
$V_F = V_{EC}$	I _F = 25 A	T _j = 25 °C				٧
	$V_{GE} = 0 V$					V
V_{F0}		T _j = 25 °C				V
10	chiplevel	,				V
r _F	abialaval	T _j = 25 °C		0.00	0.00	mΩ
	chiplevel			0.00	0.00	mΩ
I _{RRM}		T _j = 150 °C		t.b.d.		Α
Q _{rr}	V _{GE} = -15 V	T _j = 150 °C		t.b.d.		μС
E _{rr}	VGE = 15 V	T _j = 150 °C		t.b.d.		mJ
R _{th(j-s)}	per Diode, λ _{paste} =0	.8 W/(mK)				K/W
R _{th(j-s)}	per Diode, λ _{paste} =2	.5 W/(mK)				K/W
Diode 7 -	12					
$V_F = V_{EC}$	$I_F = 25 \text{ A}$	T _j = 25 °C		2.41	2.74	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.45	2.79	V
V_{F0}	chiployel	T _j = 25 °C		1.30	1.50	V
	chiplevel	T _j = 150 °C		0.90	1.10	V
r _F	chiplevel	T _j = 25 °C		44	50	mΩ
		T _j = 150 °C		62	68	mΩ
I _{RRM}	$I_F = 25 \text{ A}$	T _j = 150 °C		23		Α
Q _{rr}	$di/dt_{off} = 732 \text{ A/}\mu\text{s}$ $V_{GE} = -15 \text{ V}$	T _j = 150 °C		3.8		μС
E _{rr}	V _{CC} = 600 V	T _j = 150 °C		1.4		mJ
R _{th(j-s)}	per Diode, λ _{paste} =0	.8 W/(mK)		1.6		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2	.5 W/(mK)		1.37		K/W
Module	_					
L _{CE}				-		nH
Ms	to heat sink		2		2.5	Nm
W				55		g
Temperat	ure Sensor					1
R ₁₀₀	T _r =100°C (R ₂₅ =10		1670 ± 3%		Ω	
R _(T)	$R_{(T)}$ =1000 Ω [1+A(T , A = 7.635*10 ⁻³ °C B = 1.731*10 ⁻⁵ °C ⁻²	T-25°C)+B(T-25°C) ²] -1 °C ⁻¹ , °C ⁻²				



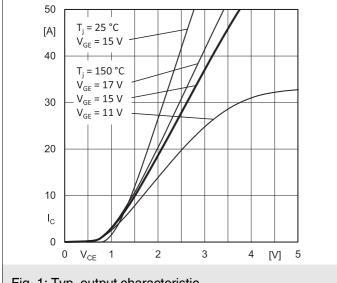


Fig. 1: Typ. output characteristic

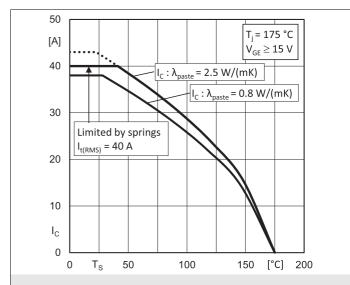


Fig. 2: Rated current vs. temperature Ic = f (Ts)

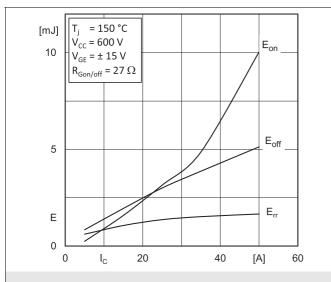


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

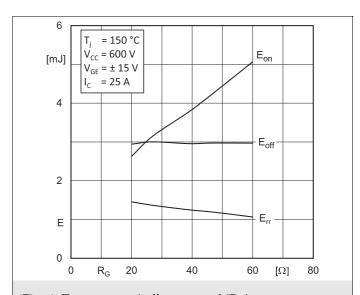


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

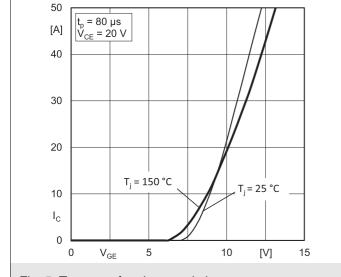


Fig. 5: Typ. transfer characteristic

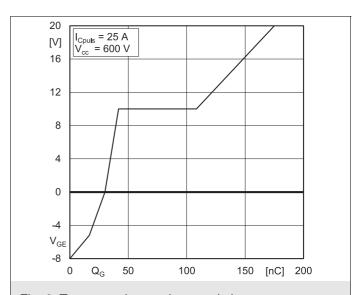


Fig. 6: Typ. gate charge characteristic

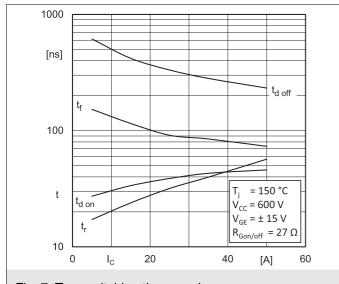


Fig. 7: Typ. switching times vs. I_C

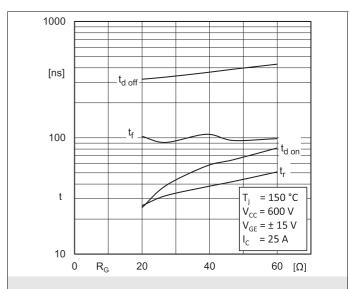


Fig. 8: Typ. switching times vs. gate resistor R_{G}

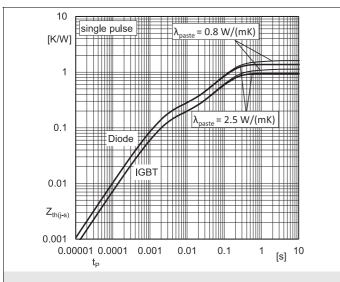


Fig. 9: Typ. transient thermal impedance

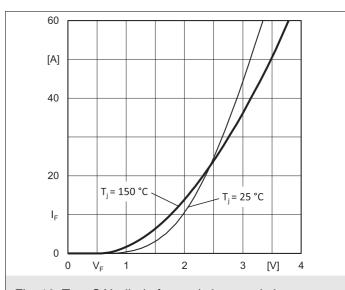


Fig. 10: Typ. CAL diode forward characteristic

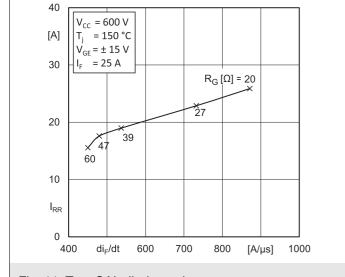


Fig. 11: Typ. CAL diode peak reverse recovery current

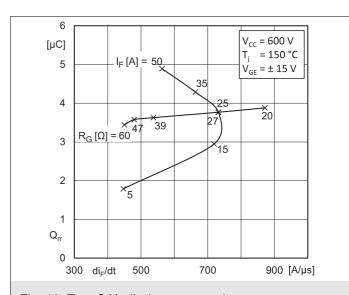
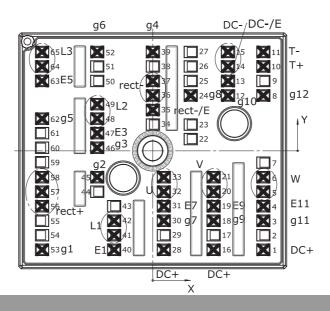


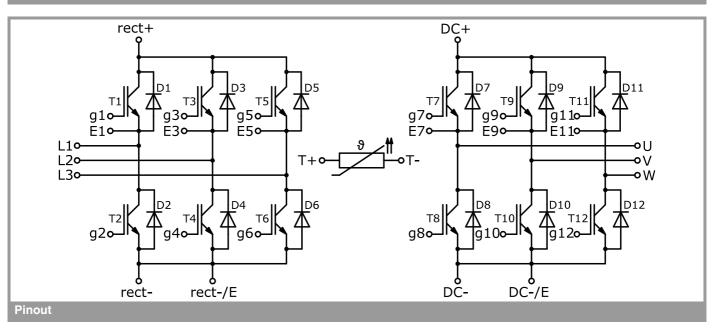
Fig. 12: Typ. CAL diode recovery charge

Pin out											
Pin	Χ	Y	Function	Pin	X	Υ	Function	Pin	X	Y	Function
1	24,38		DC+	23	8,38	5,80		45	-12,23	-5,80	g2
2	24,38	-18,60		24	8,38	12,20	g8	46	-12,23	0,70	g3
3	24,38	-15,40	g11	25	8,38	15,40		47	-12,23	3,90	E3
4	24,38	-12,20	E11	26	8,38	18,60		48	-12,23	7,10	L2
5	24,38		W	27	8,38	21,80		49	-12,23	10,30	L2
6	24,38		W	28	2,46		DC+	50	-12,23		
7	24,38			29	2,46			51	-12,23		
8	24,38		g12	30	2,46		g7	52	-12,23		
9	24,38	15,40		31	2,46	-12,20	E7	53	-24,38	-21,80	g1
10	24,38	18,60	T+	32	2,46	-9,00	U	54	-24,38	-18,60	
11	24,38		T-	33	2,46		U	55	-24,38		
12	16,58	12,20	g10	34	0,03			56	-24,38	-12,20	rect+
13	16,58	15,40	DC-/E	35	0,03	9,00	rect-/E	57	-24,38	-9,00	rect+
14	16,58	18,60	DC-	36	0,03	12,20	rect-	58	-24,38	-5,80	rect+
15	16,58	21,80	DC-	37	0,03	15,40	rect-	59	-24,38	-2,50	
16	13,42	-21,80	DC+	38	0,03	18,60		60	-24,38		
17	13,42	-18,60		39	0,03	21,80	g4	61	-24,38		
18	13,42	-15,40	g9	40	-8,51	-21,80	E1	62	-24,38	7,10	g5
19	13,42	-12,20	E9	41	-8,51	-18,60	L1	63	-24,38	15,40	E5
20	13,42	-9,00	V	42	-8,51	-15,40	L1	64	-24,38	18,60	L3
21	13,42	-5,80	V	43	-8,51	-12,20		65	-24,38	21,80	L3
22	8,38	2,60		44	-12,23	-9,00					

all values in mm



Pinout and Dimensions



This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

*IMPORTANT INFORMATION AND WARNINGS

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